## **Supplementary Information**

# Tin(II) Precursor is an Active Site to determine the Crystal Framework in

## CsSnI<sub>3</sub> Perovskite

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### **ADDITIONAL EXPERIMENTS**

### **Additional Materials**

Poly(3,4-ethylenedioxythiophene) polystyrene sulfonate (PEDOT:PSS, Clevios<sup>TM</sup> P VP AI 4083) was purchased from Heraeus. Phenyl-C61-butyric acid methyl ester (PC<sub>61</sub>BM) was purchased from Organic Semiconductor Materials (OSM Co., Ltd.). Bathocuproine (BCP, 98 %) was obtained from Alfa Aesar. Chlorobenzene (anhydrous,  $\geq$  99.8 %) and Isopropanol (anhydrous,  $\geq$  99.5 %) were obtained from Sigma-Aldrich and used for PC<sub>61</sub>BM and BCP solution, respectively.

#### **Preparation of Perovskite Precursor Solutions**

A CsSnI<sub>3</sub> perovskite precursor solution including each precursor such as CsI, SnI<sub>2</sub>, or SnF<sub>2</sub> was prepared as dissolving the materials in DMF, DMSO, or DMF:DMSO (1:4 v/v) mixed solvent. The precursor solutions were stirred on the hot plate under the 50 °C heating condition in the N<sub>2</sub>-filled glove box.

# Crystal Growth of Sn<sup>2+</sup> Precursor-based Crystals or CsSnI<sub>3</sub> perovskites with ATMS

 $SnI_2$  (0.298 g - 0.8 M concentration) +  $SnF_2$  (0.026 g - 0.16 M concentration) precursor solutions with various ATMS amount (0.1, 0.5, 1, 2, 4, and 8 % v/v) were prepared under the 50 °C heating temperature in the N<sub>2</sub>-filled glove-box for 2 h. The precursor solutions were spincast onto the indium tin oxide (ITO)/PEDOT:PSS substrate with a spinning speed of 1000 rpm (10 s) and 5000 rpm (45 s). The deposited tin precursor layer was aged at room temperature for 30 min and annealed at 70 °C for 10 min. With a similar method, the CsSnI<sub>3</sub> crystal film including ATMS anion was generated from a CsSnI<sub>3</sub> + ATMS precursor solution. The crystal was grown on the ITO/PEDOT:PSS substrate by spin-coating and annealing process.

### Fabrication of CsSnI<sub>3</sub> Perovskite Solar Cells

An ITO-coated glass substrate was sequentially cleaned under ultra-sonication with acetone

and isopropyl alcohol for 30 min, respectively. The cleaned-ITO substrate was treated with UV ozone for 20 min to remove additional alien materials on the surface of the substrate. A PEDOT:PSS that have storage in the refrigerator at ca. 5 °C was spin-cast onto the pretreated ITO substrate with a ~ 40 nm thickness in the air. The ITO/PEDOT:PSS substrate was transferred to the N<sub>2</sub>-filled glove box. A perovskite precursor solution (SnI<sub>2</sub> + SnF<sub>2</sub> or CsSnI<sub>3</sub>) was prepared with proper concentration and/or stoichiometric ratio under 50 °C temperature. The solution was deposited onto the ITO/PEDOT:PSS substrate with a 0.2 µm filtration by spin-coating, the perovskite-coated substrate was subsequently annealed on the hot plate. A PC<sub>61</sub>BM layer (20 mg ml<sup>-1</sup> concentration in chlorobenzene) was deposited above the perovskite crystal film with a spinning rate of 1500 rpm and annealed at 70 °C for 10 min. Finally, a ca. 120 nm of silver (Ag) was deposited as a top electrode by thermal evaporation under 1.2 ×  $10^{-5}$  Torr.

#### **General Characterization**

UV-vis absorption spectra with a baseline correction were recorded using a UV-2700 spectrometer (Shimadzu, Japan). The measurement system was two-detector absorbance mode and the slit width was 5 nm. Scan speed and data intervals were 100 nm/min (medium) and 0.05 nm, respectively. For the solution samples, perovskite precursor solutions were filled in a quartz cuvette with a path length of 10 nm and measured. Perovskite film was coated onto the ITO/PEDOT:PSS substrate and scanned as a solid state. A DMF or DMSO solution and ITO/PEDOT:PSS substrate were used as a reference sample for the solution and solid system, respectively.

Transmission electron microscopy (TEM) was conducted to obtain lattice phases of perovskite crystals at a solution or solid state. JEOL-2100F or JEM-F200 instrument equipped with a high-angle annular dark-field (HAADF) was operated at an acceleration voltage of 200 kV. The high-resolution (HR) TEM images were recorded at various focus and magnification

(1.0, 1.2, or 1.5 M) conditions. For the solution samples, perovskite precursor dispersions were diluted 1/6 in DMF:DMSO (1:4) mixed solution, and they were dropped onto the carbon support film grids (300 mesh, Cu). For the film samples, perovskite crystals that were grown on the ITO/PEDOT:PSS substrate were scratched and dropped onto the same grids as the solution sample. A droplet of anti-solvent was dropped onto the grid to fix the scratched powders. Samples were dried in vacuum condition for over 70 h before loading into the TEM instrument. All the TEM sample preparation processes were conducted in the N<sub>2</sub>-filled glovebox.

Attenuated total reflectance Fourier transform infrared (ATR-FTIR) spectra were recorded on a TENSOR 27 (Bruker, Germany) with a platinum ATR accessory at room temperature. A DLATGS detector that provides a resolution of 4 cm<sup>-1</sup> was used and scan time was 32. The liquid samples were filled into the ATR accessory with ca. 300  $\mu$ l, and then measured.

<sup>1</sup>H NMR and <sup>119</sup>Sn NMR spectra of the perovskite precursor samples were recorded by using an AvanceIII 500 MHz spectrometer (Bruker, Germany) with a 5 mm HR-MAS probe. The samples were dispersed in DMSO-d<sub>6</sub> solvent (concentration = 0.75 mL) and filled into the NMR tube to measure. Tetramethyltin was used as a reference for the <sup>119</sup>Sn NMR measurements.

A New D8-Advance X-ray diffractometer (Cu K $\alpha$  radiation, 8.04 keV) equipped with a diffracted beam monochromator was employed to measure the crystal diffraction patterns of perovskite films. All XRD data were recorded with a coupled two theta (2 $\theta$ )/theta mode in the 2 $\theta$  range from 10° to 50° at room temperature. The scanning rate was 2° min<sup>-1</sup> and the X-ray exposure time per point was 0.5 s.

The surface morphologies of perovskite films were investigated by field emission scanning electron microscopy (FE-SEM) using a JSM-7100F (JEOL, Ltd.) instrument. An acceleration voltage was 20 kV and the focused images were obtained at various magnifications.

Transmission small-angle X-ray scattering (SAXS) measurements were conducted at the 4C SAXS-II beamline of the PLS-II synchrotron facility, Pohang Accelerator Laboratory (Pohang, Korea). The X-ray beam with an energy of 16.09 keV was used, and scattering data were collected with a two-dimensional charged-coupled detector (CCD: model Rayonix 2D SX 165). The beam was exposed to solution samples in 1.5 mm quartz capillaries and the exposure time was set to 10 s for each sample. The capillary cell (a thickness of 0.01 mm and an external diameter of 1.5 mm, Charle Supper Company) was placed in a metal holder with a lateral direction to eliminate the thickness effect of the capillary cell. When the solution was changed, the cell was washed to di-water and acetone 3 times. Sample-to-detector distance (SDD) was 1.0 m with a confidence interval, 0.032 Å<sup>-1</sup> < q < 0.700 Å<sup>-1</sup>. The scattering angles were calibrated by using a pre-calibrated Ti-SBA-15 (Sigma-Aldrich) and silver behenate (Tokyo Chemical Industry) as standards. Buffer solutions (DMF, DMSO, or DMF:DMSO) were separately measured and substrated from perovskite solutions in SAXS data treatment.

#### **Device Characterization**

All device measurements were carried out in ambient conditions (room temperature and relative humidity (RH) of 30 - 35 %). Current-voltage (*J-V*) characteristics of solar cell devices were measured using a solar simulator (PEC-L01, Peccell Technologies) under standard AM1.5 illumination (100 mW cm<sup>-2</sup>). The light source was calibrated with a silicon photodiode detector (BS-500BK, BUNKOUKEIKI CO., LTD.). Each device was measured with a scan rate of 100 mV s<sup>-1</sup> using a Keithley 2400 source meter. The external quantum efficiency (EQE) spectra were characterized using a CompactStat instrument (Ivium Technologies; Eindhoven, Netherlands) with a power source (Abet Technologies 150 W xenon lamp, 13014) and a monochromator (DongWoo Opteron, MonoRa500i). The system was calibrated with the same photodiode detector for the solar simulator.



Fig. S1 UV-vis absorption spectra of  $CsSnI_3$  precursor solution dissolved in DMF:DMSO mixed solvent with 1:4 volume ratio at various measurement conditions that control the solution concentration: (a) 0.32 mM, (b) 0.16 mM, and (c) 0.08 mM.



**Fig. S2** Transmission SAXS results with the theoretical X-ray transmission factor for DMF solvent: (a) X-ray photon energy versus transmission curve, (b) two-dimensional diffraction patterns, and (c) corresponding average radial integrations.



**Fig. S3** Transmission SAXS results with the theoretical X-ray transmission factor for DMSO solvent: (a) X-ray photon energy versus transmission curve, (b) 2D diffraction patterns, and (c) corresponding average 1D profiles.



Fig. S4 Transmission SAXS results for DMF:DMSO mixed solvent: (a) two-dimensional diffraction patterns, and (c) corresponding average 1D integrated plots.



Fig. S5 <sup>1</sup>H NMR spectrum of ATMS sample in deuterated DMSO-d<sub>6</sub> solution.



Fig. S6 <sup>1</sup>H NMR spectrum of CsSnI<sub>3</sub> - ATMS sample in deuterated DMSO-d<sub>6</sub> solution.



Fig. S7 <sup>119</sup>Sn NMR spectrum of CsSnI<sub>3</sub> perovskite in deuterated DMSO-d<sub>6</sub> solution.



Fig. S8  $^{119}$ Sn NMR spectrum of CsSnI<sub>3</sub> perovskite precursor with ATMS anion in deuterated DMSO-d<sub>6</sub> solution.



Fig. S9  $^{119}$ Sn NMR spectrum of SnI<sub>2</sub> precursor with SnF<sub>2</sub> in deuterated DMSO-d<sub>6</sub> solution.



Fig. S10  $^{119}$ Sn NMR spectrum of SnI<sub>2</sub> + SnF<sub>2</sub> sample with ATMS anion in deuterated DMSOd<sub>6</sub> solution.



**Fig. S11** Partial magnification spectra from Figure 3d with a range of (a) 1200 - 800 cm<sup>-1</sup> and (b) 2490 - 2140 cm<sup>-1</sup>.



Fig. S12 Magnification of FTIR spectra from Figure 3e with a range from 2160 to 2500 cm<sup>-1</sup>.



**Fig. S13** (a) Magnified XRD results from Fig. 4c to highlight the (100) crystal lattice peak. (b) The trends of FWHM and corresponding calculated crystal size of  $SnI_2 + SnF_2$  precursor as a function of ATMS concentration.



Fig. S14 A XRD pattern of  $SnI_2 + SnF_2$  precursor film with ATMS of 8% concentration.



**Fig. S15** CsSnI<sub>3</sub> crystal structures with ATMS anion of 1% (a-d) and 4% (e-h) concentrations. They were created from a conventional (mixed single - CsSnI<sub>3</sub> + ATMS) solution: (a-b and e-f) SEM images. Two images for each condition have different magnifications. The scale bar is 1  $\mu$ m. (c-d and g-h) TEM images. Two images for each condition were measured by 1.0 M (left) and 1.2 M (right) magnification. Yellow circle dash lines show the collapsed crystal lattices in the CsSnI<sub>3</sub> phase.



**Fig. S16** Large-sized TEM image (raw data) of the synthesized CsSnI<sub>3</sub> perovskite crystal with the conventional method.



Fig. S17 Large-sized TEM image (raw data) of the synthesized  $CsSnI_3$  perovskite crystal with the two-step process.